(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
6 January 2005 (06.01.2005)

PCT

(10) International Publication Number
WO 2005/001908 A2

(51) International Patent Classification[7]: H01L 21/00

(21) International Application Number:
PCT/US2004/017727

(22) International Filing Date: 5 June 2004 (05.06.2004)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
10/601,401 23 June 2003 (23.06.2003) US

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(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

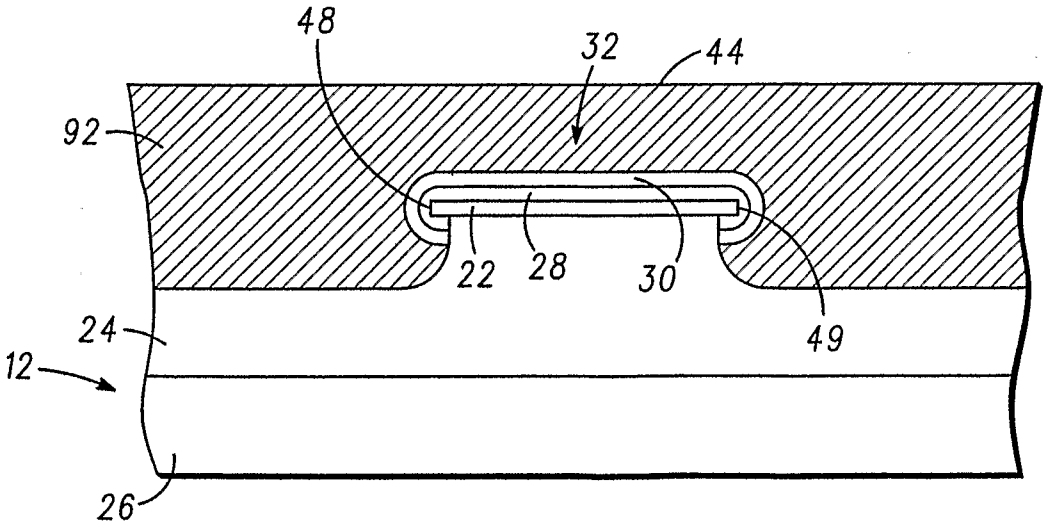
(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

— *without international search report and to be republished upon receipt of that report*

[Continued on next page]

(54) Title: SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURE



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(57) Abstract: A strained semiconductor device suitable for use in an integrated circuit and a method for manufacturing the strained semiconductor device. A mesa isolation structure is formed from a semiconductor on-insulator substrate. A gate structure is formed on the mesa isolation structure. The gate structure includes a gate disposed on a gate dielectric material and has two sets of opposing sidewalls. Semiconductor material is selectively grown on portions of the mesa isolation structure adjacent a first set of opposing sidewalls of the gate structure and then doped. The doped semiconductor material is silicided and protected by a dielectric material. The gate is silicided wherein the silicide wraps around a second set of opposing sidewalls and stresses a channel region of the semiconductor device.

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